

HEF4511B

BCD to 7-segment latch/decoder/driver

Rev. 06 — 7 December 2009

Product data sheet

1. General description

The HEF4511B is a BCD to 7-segment latch/decoder/driver with four address inputs (D0 to D3), an active HIGH latch enable input (LE), an active LOW ripple blanking input ($\overline{\text{BL}}$), an active LOW lamp test input ($\overline{\text{LT}}$), and seven active HIGH NPN bipolar transistor segment outputs (Qa to Qg).

When LE is LOW and $\overline{\text{BL}}$ is HIGH, the state of the segment outputs (Qa to Qg) is determined by the data on D0 to D3. When LE goes HIGH, the last data present on D0 to D3 is stored in the latches and the segment outputs remain unchanged. When $\overline{\text{LT}}$ is LOW, all of the segment outputs are HIGH independent of all other input conditions. With $\overline{\text{LT}}$ HIGH, a LOW on $\overline{\text{BL}}$ forces all segment outputs LOW. The inputs $\overline{\text{LT}}$ and $\overline{\text{BL}}$ do not affect the latch circuit.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input. It is also suitable for use over the industrial ($-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$) and automotive ($-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$) temperature ranges.

2. Features

- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Operates across the automotive temperature range $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Complies with JEDEC standard JESD 13-B

3. Applications

- Automotive and industrial

4. Ordering information

Table 1. Ordering information

All types operate from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$.

Type number	Package		
	Name	Description	Version
HEF4511BP	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
HEF4511BT	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1

5. Functional diagram

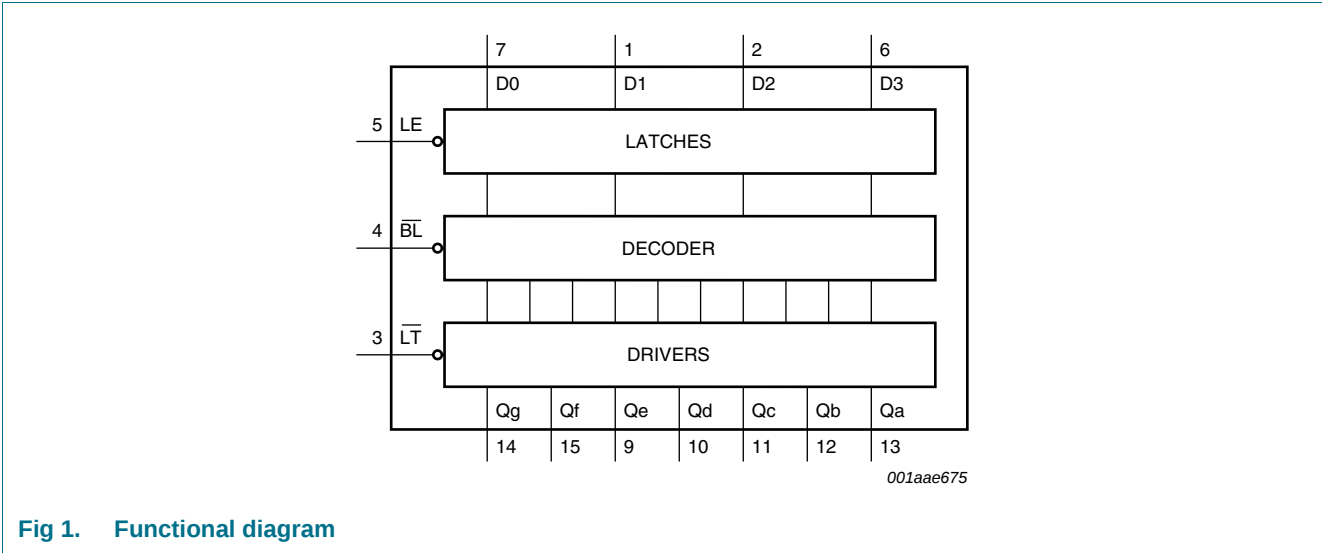


Fig 1. Functional diagram

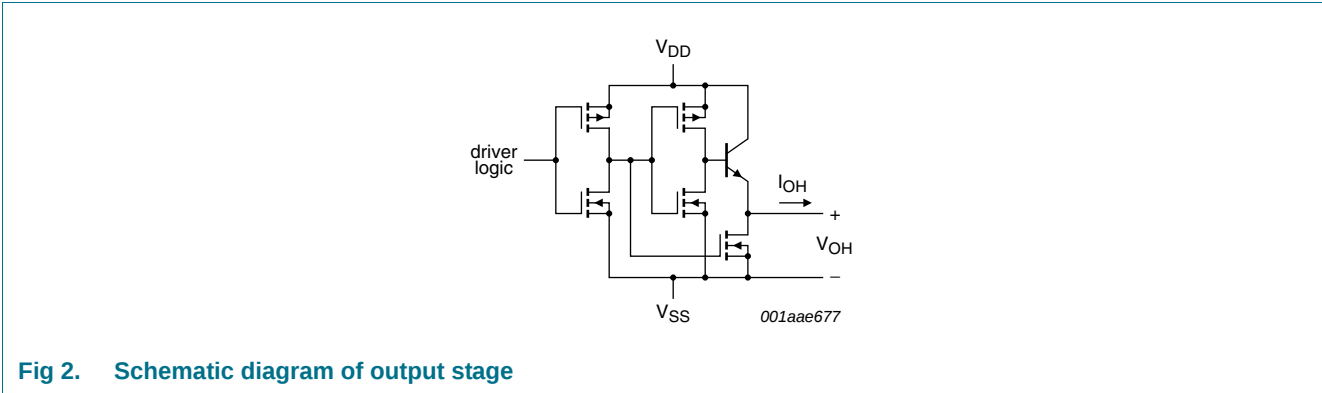


Fig 2. Schematic diagram of output stage

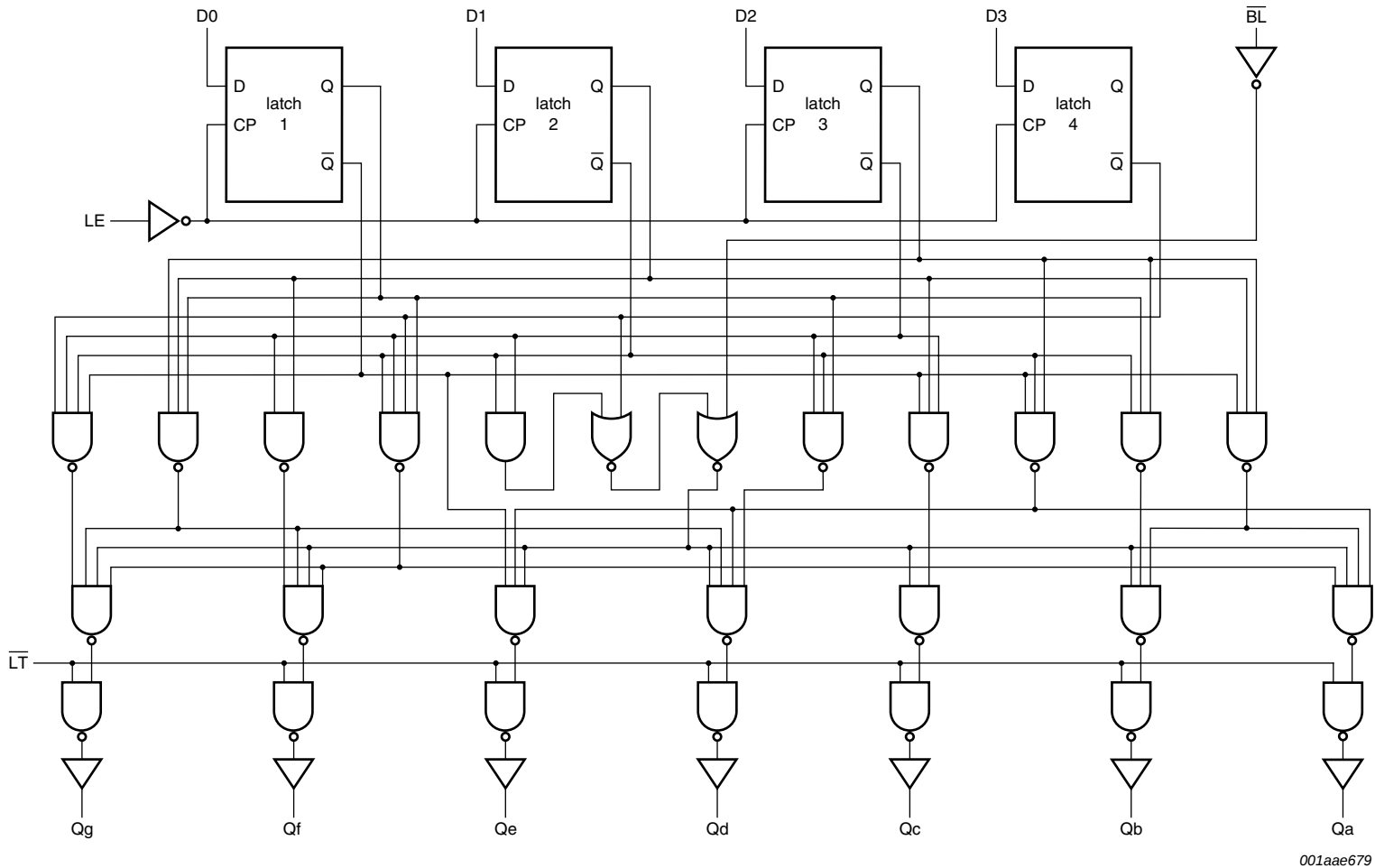


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

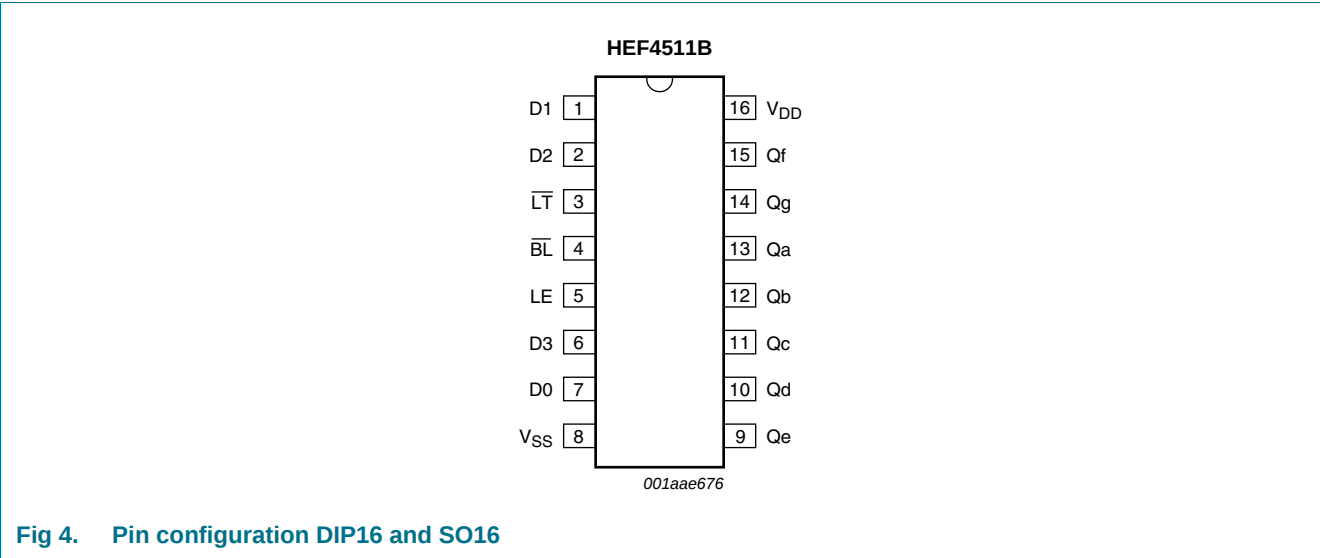


Fig 4. Pin configuration DIP16 and SO16

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{\text{LT}}$	3	lamp test input (active LOW)
$\overline{\text{BL}}$	4	ripple blanking input (active LOW)
LE	5	latch enable input (active HIGH)
D0 to D3	7, 1, 2, 6	address (data) input
V _{SS}	8	ground supply voltage
Qa to Qg	13, 12, 11, 10, 9, 15, 14	segment output
V _{DD}	16	supply voltage

7. Functional description

Table 3. Function table^[1]

Inputs							Outputs							Display
LE	BL	LT	D3	D2	D1	D0	Qa	Qb	Qc	Qd	Qe	Qf	Qg	
X	X	L	X	X	X	X	H	H	H	H	H	H	H	8
X	L	H	X	X	X	X	L	L	L	L	L	L	L	blank
L	H	H	L	L	L	L	H	H	H	H	H	H	L	0
L	H	H	L	L	L	H	L	H	H	L	L	L	L	1
L	H	H	L	L	H	L	H	H	L	H	H	L	H	2
L	H	H	L	L	H	H	H	H	H	H	L	L	H	3
L	H	H	L	H	L	L	L	H	H	L	L	H	H	4
L	H	H	L	H	L	H	H	L	H	H	L	H	H	5
L	H	H	L	H	H	L	L	L	H	H	H	H	H	6
L	H	H	L	H	H	H	H	H	H	L	L	L	L	7
L	H	H	H	L	L	L	H	H	H	H	H	H	H	8
L	H	H	H	L	L	H	H	H	H	L	L	H	H	9
L	H	H	H	L	H	X	L	L	L	L	L	L	L	blank
L	H	H	H	H	X	X	L	L	L	L	L	L	L	blank
H	H	H	X	X	X	X	N.C.	N.C.	N.C.	N.C.	N.C.	N.C.	N.C.	N.C.

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; N.C. = no change.

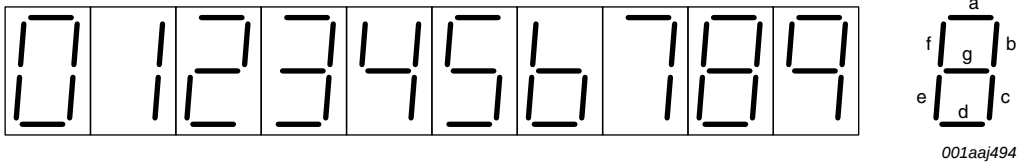


Fig 5. Seven segment digital display with segment designation

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{DD} + 0.5\text{ V}$	-	± 10	mA
V_I	input voltage		-0.5	$V_{DD} + 0.5$	V
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{DD} + 0.5\text{ V}$	-	± 10	mA
$I_{I/O}$	input/output current		-	± 10	mA
I_{OH}	HIGH-level output current		[1] -25	-	mA
I_{DD}	supply current		-	50	mA
T_{stg}	storage temperature		-65	+150	°C
T_{amb}	ambient temperature		-40	+125	°C
P_{tot}	total power dissipation	$T_{amb} = 125\text{ °C}$			
		DIP16 package	[2] -	750	mW
		SO16 package	[3] -	500	mW
P	power dissipation	per output	-	100	mW

[1] A destructive high current mode may occur if V_I and V_O are not constrained to the range $V_{SS} \leq V_I$ or $V_O \leq V_{DD}$.

[2] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

[3] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DD}	supply voltage		3	-	15	V
V_I	input voltage		0	-	V_{DD}	V
T_{amb}	ambient temperature	in free air	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5\text{ V}$	-	-	3.75	$\mu\text{s/V}$
		$V_{DD} = 10\text{ V}$	-	-	0.5	$\mu\text{s/V}$
		$V_{DD} = 15\text{ V}$	-	-	0.08	$\mu\text{s/V}$

10. Static characteristics

Table 6. Static characteristics

$V_{SS} = 0\text{ V}$; $V_I = V_{SS}$ or V_{DD} ; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	$T_{amb} = -40\text{ °C}$		$T_{amb} = +25\text{ °C}$		$T_{amb} = +85\text{ °C}$		$T_{amb} = +125\text{ °C}$		Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	$ I_O < 1\text{ }\mu\text{A}$	5 V	3.5	-	3.5	-	3.5	-	3.5	-	V
			10 V	7.0	-	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level input voltage	$ I_O < 1\text{ }\mu\text{A}$	5 V	-	1.5	-	1.5	-	1.5	-	1.5	V
			10 V	-	3.0	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	-	4.0	V
V_{OH}	HIGH-level output voltage	see Table 7	-	-	-	-	-	-	-	-	-	-
V_{OL}	LOW-level output voltage	$ I_O < 1\text{ }\mu\text{A}$	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V
I_{OH}	HIGH-level output current	$V_O = 2.5\text{ V}$	5 V	-1.7	-	-1.4	-	-1.1	-	-1.1	-	mA
		$V_O = 4.6\text{ V}$	5 V	-0.64	-	-0.5	-	-0.36	-	-0.36	-	mA
		$V_O = 9.5\text{ V}$	10 V	-1.6	-	-1.3	-	-0.9	-	-0.9	-	mA
		$V_O = 13.5\text{ V}$	15 V	-4.2	-	-3.4	-	-2.4	-	-2.4	-	mA
I_{OL}	LOW-level output current	$V_O = 0.4\text{ V}$	5 V	0.64	-	0.5	-	0.36	-	0.36	-	mA
		$V_O = 0.5\text{ V}$	10 V	1.6	-	1.3	-	0.9	-	0.9	-	mA
		$V_O = 1.5\text{ V}$	15 V	4.2	-	3.4	-	2.4	-	2.4	-	mA
I_I	input leakage current		15 V	-	± 0.1	-	± 0.1	-	± 1.0	-	± 1.0	μA
I_{DD}	supply current	$I_O = 0\text{ A}$	5 V	-	5	-	5	-	150	-	150	μA
			10 V	-	10	-	10	-	300	-	300	μA
			15 V	-	20	-	20	-	600	-	600	μA
C_I	input capacitance		-	-	-	-	7.5	-	-	-	-	pF

Table 7. Static characteristics for V_{OH} $V_{SS} = 0\text{ V}$.

Symbol	Parameter	I_{OH}	V_{DD}	$T_{amb} = -40\text{ °C}$	$T_{amb} = +25\text{ °C}$		$T_{amb} = +85\text{ °C}$	$T_{amb} = +125\text{ °C}$	Unit
		mA	V	Min	Min	Typ	Min	Min	
V_{OH}	HIGH-level output voltage	0	5 V	4.10	4.10	4.40	4.10	4.10	V
			10 V	9.10	9.10	9.90	9.10	9.10	V
			15 V	14.10	14.10	14.40	14.10	14.10	V
		5	5 V	-	-	4.30	-	-	V
			10 V	-	-	9.30	-	-	V
			15 V	-	-	14.30	-	-	V
		10	5 V	3.60	3.60	4.25	3.30	3.20	V
			10 V	8.75	8.75	9.25	8.45	8.35	V
			15 V	13.75	13.75	14.30	13.45	13.35	V
		15	5 V	-	-	4.20	-	-	V
			10 V	-	-	9.20	-	-	V
			15 V	-	-	14.20	-	-	V
		20	5 V	2.80	2.80	4.20	2.50	2.30	V
			10 V	8.10	8.10	9.20	7.80	7.60	V
			15 V	13.10	13.10	14.20	12.80	12.60	V
		25	5 V	-	-	4.15	-	-	V
			10 V	-	-	9.20	-	-	V
			15 V	-	-	14.20	-	-	V

11. Dynamic characteristics

Table 8. Dynamic characteristics $V_{SS} = 0\text{ V}$; $T_{amb} = 25\text{ °C}$; for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula ^[1]	Min	Typ	Max	Unit
t_{PHL}	HIGH to LOW propagation delay	Dn → Qn; see Figure 6	5 V	$128\text{ ns} + (0.55\text{ ns/pF})C_L$	-	155	310	ns
			10 V	$49\text{ ns} + (0.23\text{ ns/pF})C_L$	-	60	120	ns
			15 V	$32\text{ ns} + (0.16\text{ ns/pF})C_L$	-	40	80	ns
		LE → Qn; see Figure 6	5 V	$133\text{ ns} + (0.55\text{ ns/pF})C_L$	-	160	320	ns
			10 V	$49\text{ ns} + (0.23\text{ ns/pF})C_L$	-	60	120	ns
			15 V	$37\text{ ns} + (0.16\text{ ns/pF})C_L$	-	45	90	ns
		$\overline{\text{BL}}$ → Qn; see Figure 6	5 V	$93\text{ ns} + (0.55\text{ ns/pF})C_L$	-	120	240	ns
			10 V	$39\text{ ns} + (0.23\text{ ns/pF})C_L$	-	50	100	ns
			15 V	$27\text{ ns} + (0.16\text{ ns/pF})C_L$	-	35	70	ns
		$\overline{\text{LT}}$ → Qn; see Figure 6	5 V	$52\text{ ns} + (0.55\text{ ns/pF})C_L$	-	80	160	ns
			10 V	$19\text{ ns} + (0.23\text{ ns/pF})C_L$	-	30	60	ns
			15 V	$12\text{ ns} + (0.16\text{ ns/pF})C_L$	-	20	40	ns

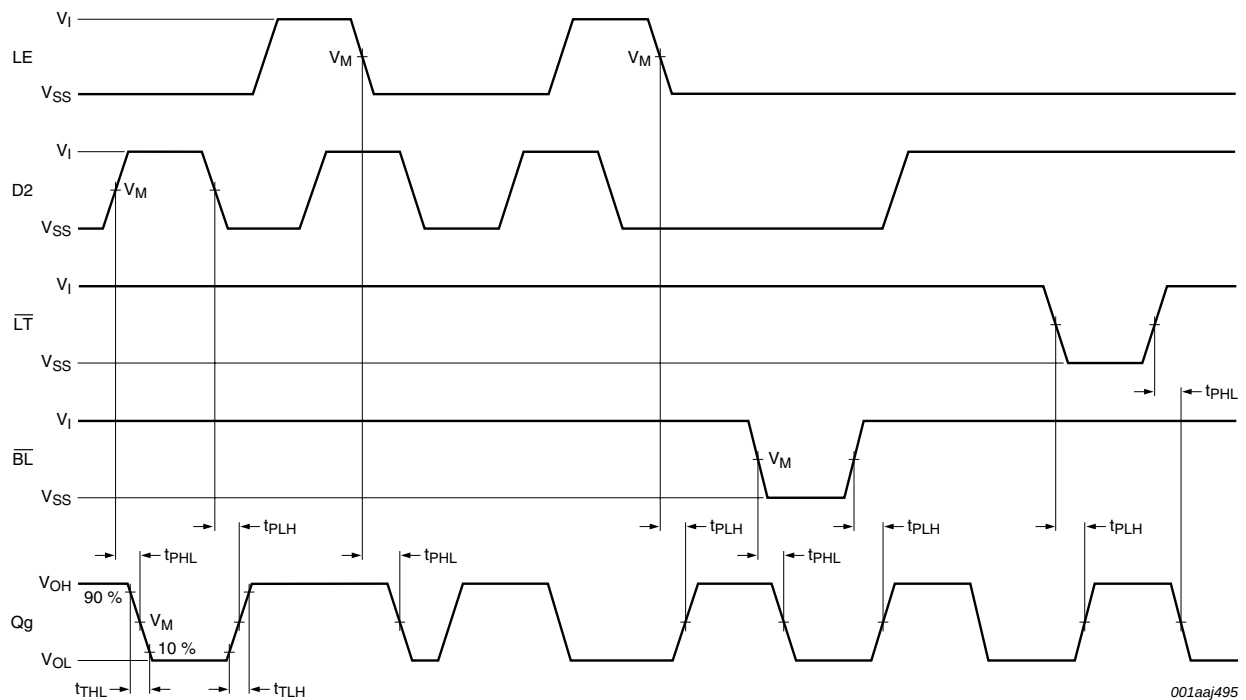
Table 8. Dynamic characteristics ...continued $V_{SS} = 0\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula ^[1]	Min	Typ	Max	Unit
t_{PLH}	LOW to HIGH propagation delay	$D_n \rightarrow Q_n$; see Figure 6	5 V	$108\text{ ns} + (0.55\text{ ns/pF})C_L$	-	135	270	ns
			10 V	$44\text{ ns} + (0.23\text{ ns/pF})C_L$	-	55	110	ns
			15 V	$32\text{ ns} + (0.16\text{ ns/pF})C_L$	-	40	80	ns
		$LE \rightarrow Q_n$; see Figure 6	5 V	$133\text{ ns} + (0.55\text{ ns/pF})C_L$	-	160	320	ns
			10 V	$59\text{ ns} + (0.23\text{ ns/pF})C_L$	-	70	140	ns
			15 V	$42\text{ ns} + (0.16\text{ ns/pF})C_L$	-	50	100	ns
		$\overline{BL} \rightarrow Q_n$; see Figure 6	5 V	$78\text{ ns} + (0.55\text{ ns/pF})C_L$	-	105	210	ns
			10 V	$29\text{ ns} + (0.23\text{ ns/pF})C_L$	-	40	80	ns
			15 V	$22\text{ ns} + (0.16\text{ ns/pF})C_L$	-	30	60	ns
		$\overline{LT} \rightarrow Q_n$; see Figure 6	5 V	$33\text{ ns} + (0.55\text{ ns/pF})C_L$	-	60	120	ns
			10 V	$19\text{ ns} + (0.23\text{ ns/pF})C_L$	-	30	60	ns
			15 V	$17\text{ ns} + (0.16\text{ ns/pF})C_L$	-	25	50	ns
t_{THL}	HIGH to LOW output transition time	see Figure 6	5 V	$10\text{ ns} + (1.00\text{ ns/pF})C_L$	-	60	120	ns
			10 V	$9\text{ ns} + (0.42\text{ ns/pF})C_L$	-	30	60	ns
			15 V	$6\text{ ns} + (0.28\text{ ns/pF})C_L$	-	20	40	ns
t_{TLH}	LOW to HIGH output transition time	see Figure 6	5 V	$20\text{ ns} + (1.00\text{ ns/pF})C_L$	-	25	50	ns
			10 V	$13\text{ ns} + (0.06\text{ ns/pF})C_L$	-	16	32	ns
			15 V	$10\text{ ns} + (0.06\text{ ns/pF})C_L$	-	13	26	ns
t_{su}	set-up time	$D_n \rightarrow LE$; see Figure 7	5 V		50	25	-	ns
			10 V		25	12	-	ns
			15 V		20	9	-	ns
t_h	hold time	$D_n \rightarrow LE$; see Figure 7	5 V		60	30	-	ns
			10 V		30	15	-	ns
			15 V		25	12	-	ns
t_w	pulse width	LE input LOW; minimum width; see Figure 7	5 V		80	40	-	ns
			10 V		40	20	-	ns
			15 V		35	17	-	ns

[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).**Table 9.** Dynamic power dissipation P_D P_D can be calculated from the formulas shown. $V_{SS} = 0\text{ V}$; $t_r = t_f \leq 20\text{ ns}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	V_{DD}	Typical formula for P_D (μW)	where:
P_D	dynamic power dissipation	5 V	$P_D = 1000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_i = input frequency in MHz;
		10 V	$P_D = 4000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_o = output frequency in MHz;
		15 V	$P_D = 10000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	C_L = output load capacitance in pF; V_{DD} = supply voltage in V; $\Sigma(f_o \times C_L)$ = sum of the outputs.

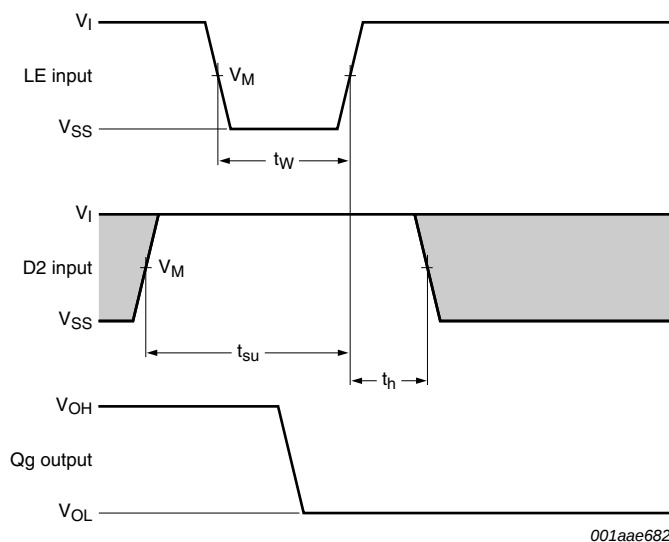
12. Waveforms



Conditions: D3 = LOW and D0 = D1 = HIGH.

Measurement points are given in [Table 10](#).

Fig 6. Propagation delays and output transition times

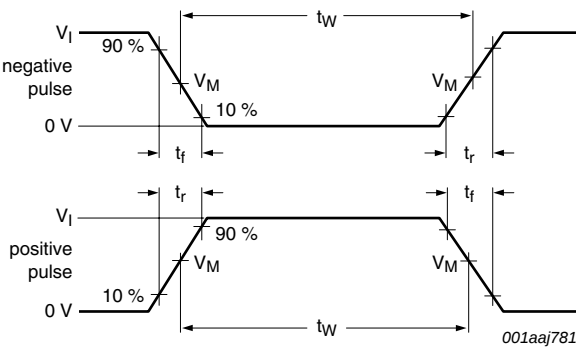


The shaded area indicates where the input is permitted to change for predictable output performance.

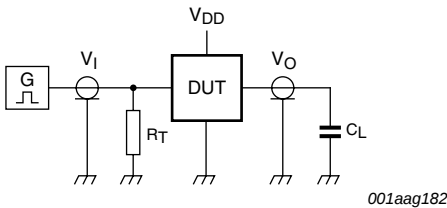
Conditions: D3 = LOW and D0 = D1 = $\overline{BL}$ = $\overline{LT}$ = HIGH.

Measurement points are given in [Table 10](#).

Fig 7. Waveforms showing minimum LE pulse width, set-up, and hold time for Dn to LE



a. Input waveforms



b. Test circuit

Test data is given in [Table 10](#).

Definitions for test circuit:

DUT = Device Under Test.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 8. Test circuit for measuring switching times

Table 10. Measurement points and test data

Supply voltage	Input			Load
	V_I	V_M	t_r, t_f	C_L
5 V to 15 V	V_{DD}	$0.5V_I$	≤ 20 ns	50 pF

13. Application information

- Driving LED displays
- Driving incandescent displays
- Driving fluorescent displays
- Driving LCD displays
- Driving gas discharge displays

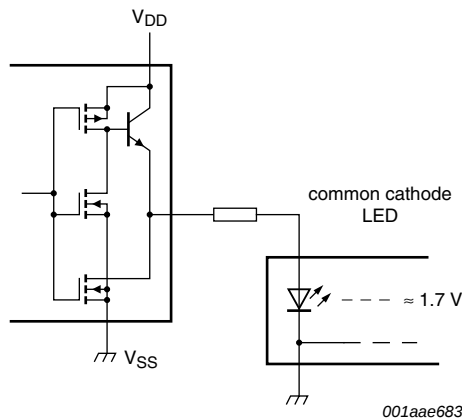


Fig 9. Connection to common cathode LED display readout

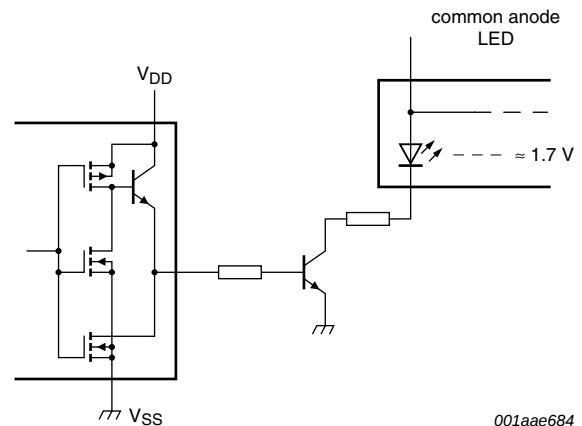
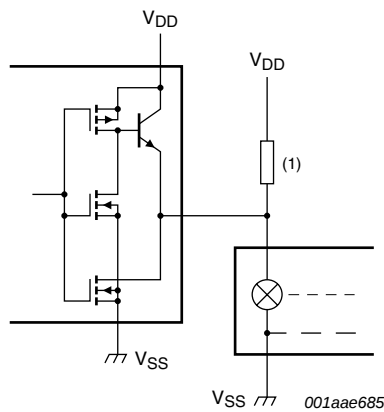


Fig 10. Connection to common anode LED display readout



(1) A filament pre-warm resistor is recommended to reduce filament thermal shock and increase the effective cold resistance of the filament.

Fig 11. Connection to incandescent display readout

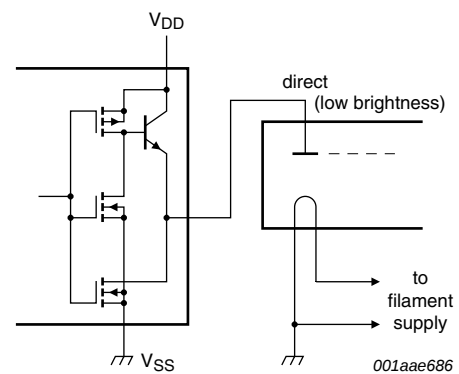


Fig 12. Connection to fluorescent display readout

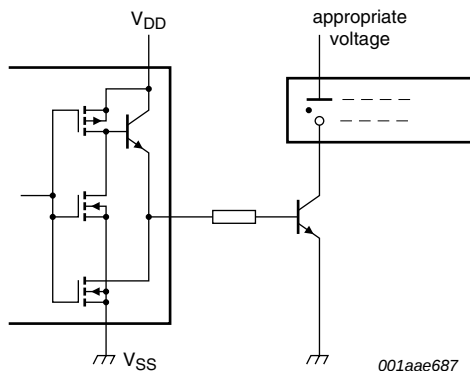
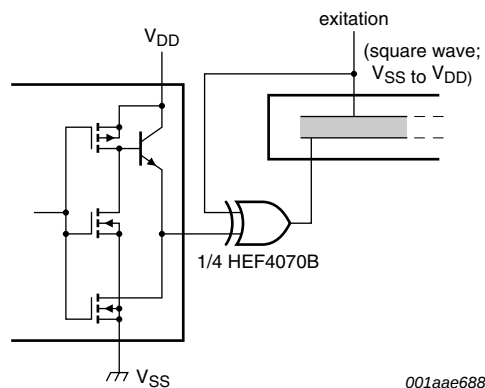


Fig 13. Connection to gas discharge display readout



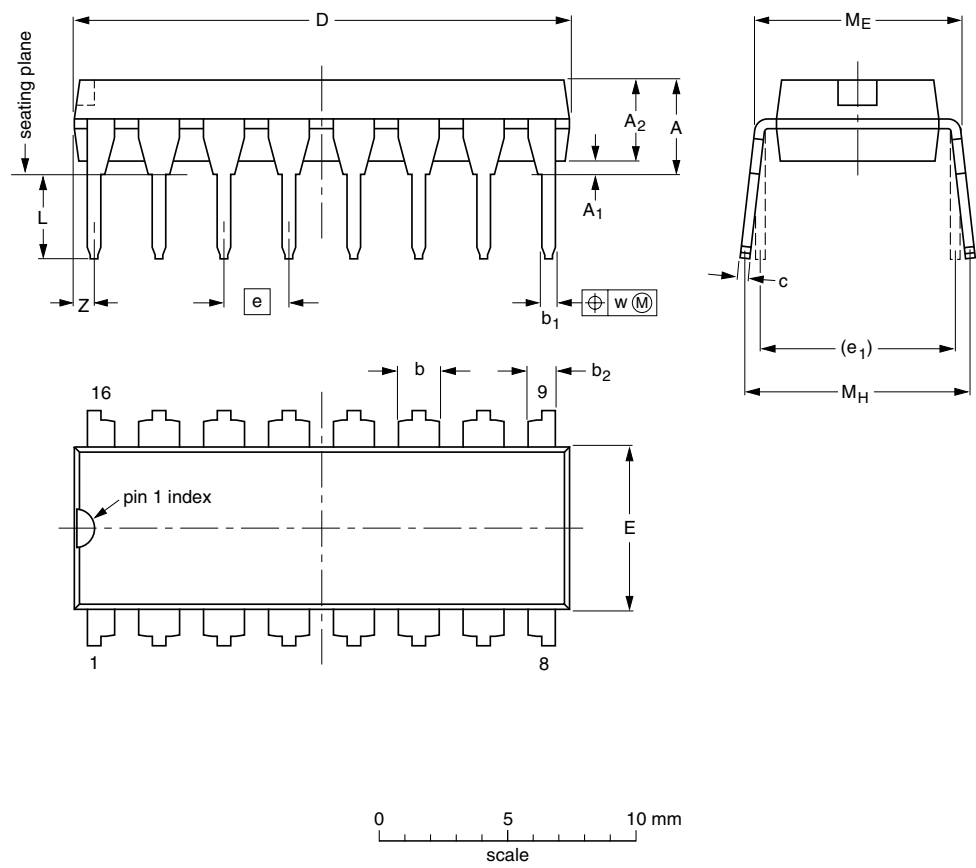
Direct DC drive of LCDs not recommended for life of LCD readouts.

Fig 14. Connection to LCD readout

14. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

Note
1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT38-4						95-01-14- 03-02-13

Fig 15. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

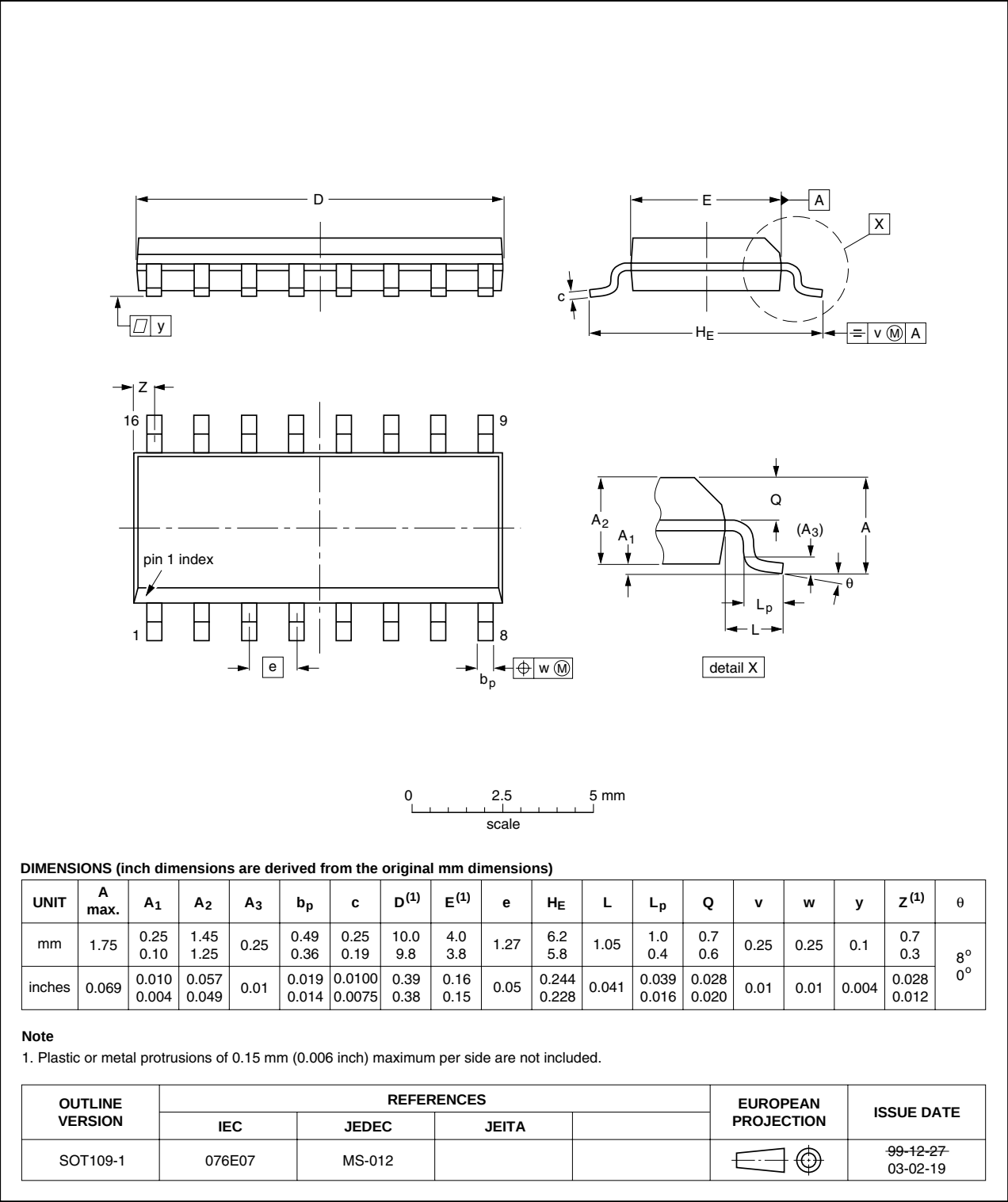


Fig 16. Package outline SOT109-1 (SO16)

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4511B_6	20091207	Product data sheet	-	HEF4511B_5
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16. Legal information

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Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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